

IN THE CLAIMS:

Claim 13 has been cancelled. Claims 1-12, and 14 have been amended herein. All of the pending claims 1 through 14 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A semiconductor device structure, comprising:
a first layer comprising anti-reflective material; and
a second layer comprising silicon nitride, located over ~~said~~ the first layer, and including at most about $1\frac{1}{4}$ in-film particles or surface roughness features per square millimeter of surface area.
2. (Currently Amended) The semiconductor device structure of claim 1, wherein ~~said~~ the anti-reflective material comprises silicon atoms and nitrogen atoms.
3. (Currently Amended) The semiconductor device structure of claim 2, wherein ~~said~~ the anti-reflective material further comprises oxygen atoms.
4. (Currently Amended) The semiconductor device structure of claim 1, wherein ~~said~~ the anti-reflective material comprises ~~Si-sub.x O-sub.y N-sub.z~~ Si_xO_yN_z, where x equals about 0.40 to about 0.65 times the sum of x, y, and z, y equals about 0.02 to about 0.56 times the sum of x, y, and z, and z equals about 0.05 to about 0.33 times the sum of x, y, and z.
5. (Currently Amended) The semiconductor device structure of claim 1, wherein a surface of ~~said~~ the first layer is substantially free of at least one of measurable particulates and surface roughness.

6. (Currently Amended) The semiconductor device structure of claim 1, wherein ~~said the~~ second layer includes at most about $1\frac{1}{4}$ of at least one of particles and surface roughness features of at least about 120 nm dimension per square millimeter of surface area.

7. (Currently Amended) The semiconductor device structure of claim 1, wherein ~~said the~~ second layer is formed on ~~said the~~ first layer.

8. (Currently Amended) A semiconductor device structure, comprising:
a first layer comprising anti-reflective material; and
a second layer comprising silicon nitride, located over ~~said the~~ first layer, and including at most about $1\frac{1}{4}$ in-film particles of surface roughness features of at least 120 nonometers size per square millimeter of surface area.

9. (Currently Amended) The semiconductor device structure of claim 8, wherein ~~said the~~ anti-reflective material comprises silicon atoms and nitrogen atoms.

10. (Currently Amended) The semiconductor device structure of claim 9, wherein ~~said the~~ anti-reflective material further comprises oxygen atoms.

11. (Currently Amended) The semiconductor device structure of claim 8, wherein ~~said the~~ anti-reflective material comprises ~~Si.sub.x O.sub.y N.sub.z~~ Si_xO_yN_z, where x equals about 0.40 to about 0.65 times the sum of x, y, and z, y equals about 0.02 to about 0.56 times the sum of x, y, and z, and z equals about 0.05 to about 0.33 times the sum of x, y, and z.

12. (Currently Amended) The semiconductor device structure of claim 8, wherein a surface of ~~said the~~ first layer is substantially free of at least one of measurable particulates and surface roughness.

13. (Cancelled)

14. (Currently Amended) The semiconductor device structure of claim 8, wherein ~~said~~ the second layer is formed on-~~said~~ the first layer.